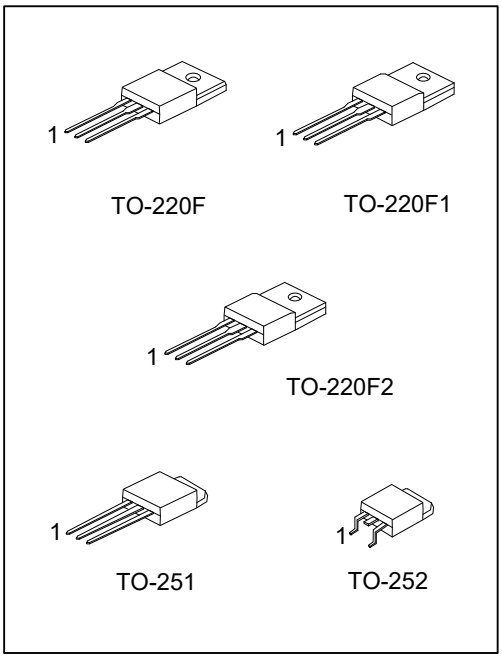
3N90-FC

Power MOSFET

3.0A, 900V N-CHANNEL POWER MOSFET



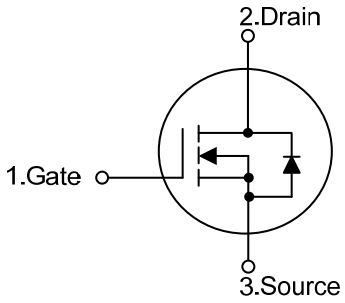
■ DESCRIPTION

The UTC **3N90-FC** provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

■ FEATURES

* $R_{DS(ON)} \leq 6.7\ \Omega$ @ V_{GS}=10V, I_D=1.5A
* Fast switching capability
* Avalanche energy specified
* Improved dv/dt capability, high ruggedness

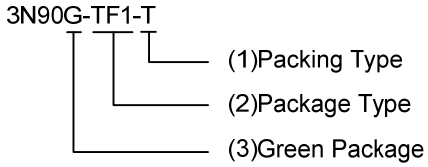
■ SYMBOL



■ ORDERING INFORMATION

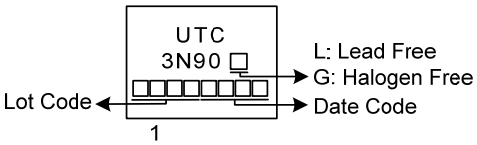
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
3N90L-TF1-T	3N90G-TF1-T	TO-220F1	G	D	S	Tube
3N90L-TF2-T	3N90G-TF2-T	TO-220F2	G	D	S	Tube
3N90L-TF3-T	3N90G-TF3-T	TO-220F	G	D	S	Tube
3N90L-TM3-T	3N90G-TM3-T	TO-251	G	D	S	Tube
3N90L-TN3-R	3N90G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



(1) T: Tube, R: Tape Reel
(2) TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2
TM3: TO-251, TN3: TO-252
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	900	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current		I_D	3	A
Pulsed Drain Current (Note 2)		I_{DM}	6	A
Avalanche Energy (Note 3)	Single Pulsed	E_{AS}	109	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.1	V/ns
Power Dissipation (T_A=25°C)	TO-220F/TO-220F1 TO-220F2	P_D	25	W
	TO-251/TO-252		44	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L=30mH, I_{AS}=2.7A, V_{DD}=50V, R_G=25 Ω, Starting T_J = 25°C
4. I_{SD} ≤ 3.0A, di/dt≤200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220F/TO-220F1 TO-220F2	θ_{JA}	62.5	°C/W
	TO-251/TO-252		110	°C/W
Junction to Case	TO-220F/TO-220F1 TO-220F2	θ_{JC}	5	°C/W
	TO-251/TO-252		2.84 (Note)	°C/W

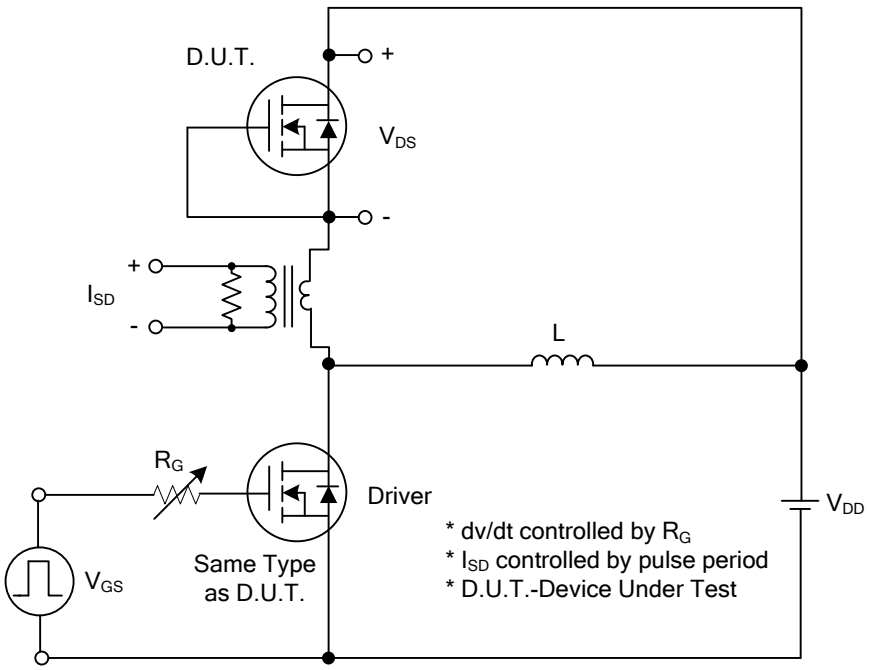
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

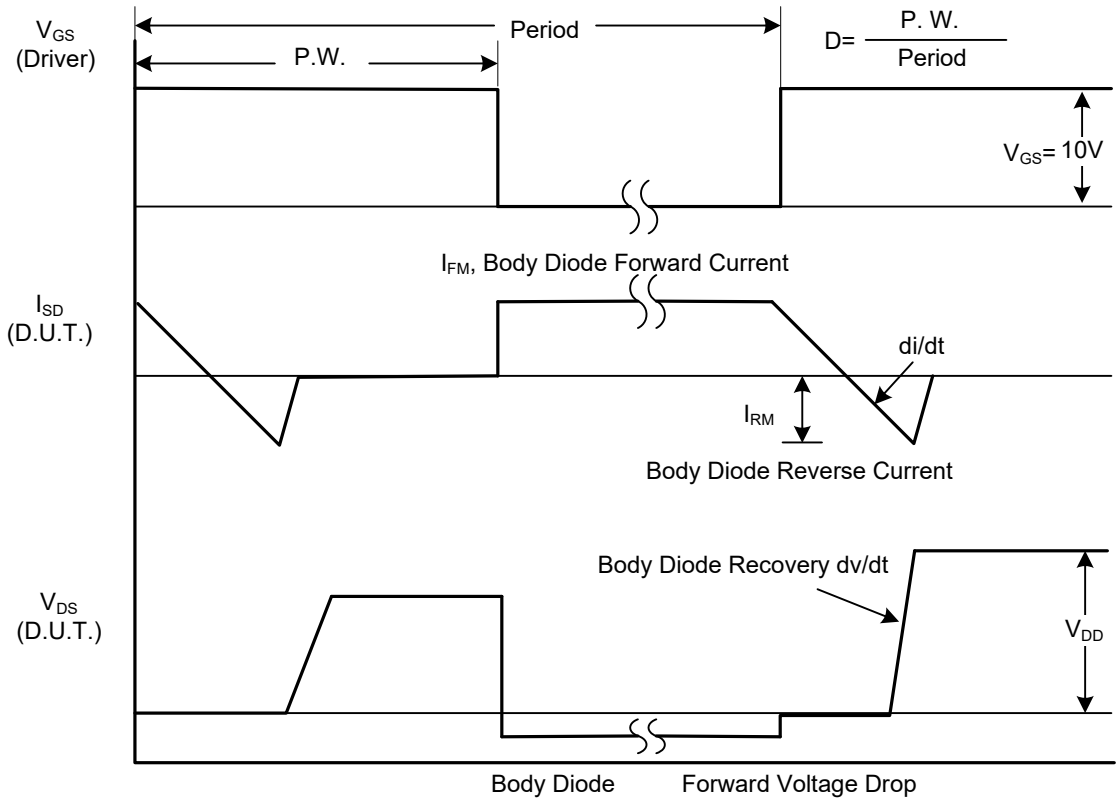
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS} = 0V, I_D = 250μA	900			V
Drain-Source Leakage Current		I_{DSS}	V_{DS} = 900V, V_{GS} = 0V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS} = 30V, V_{DS} = 0V			100	nA
	Reverse		V_{GS} = -30V, V_{DS} = 0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 250μA	3.0		5.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS} = 10V, I_D =1.5A			6.7	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{DS} =25V, V_{GS} =0V, f =1MHz		401		pF
Output Capacitance		C_{OSS}			44		pF
Reverse Transfer Capacitance		C_{RSS}			2.2		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge		Q_G	V_{DS}=720V, V_{GS}=10V, I_D=3A, I_G=1mA (Note 1, 2)		14.6		nC
Gate-Source Charge		Q_{GS}			7.3		nC
Gate-Drain Charge		Q_{GD}			1.8		nC
Turn-On Delay Time		$t_{D\ (ON)}$	V_{DD} =100V, V_{GS}=10V, I_D=3A, R_G=25Ω (Note 1, 2)		7		ns
Turn-On Rise Time		t_R			14.2		ns
Turn-Off Delay Time		$t_{D(OFF)}$			13.6		ns
Turn-Off Fall Time		t_F			25.2		ns
DRAIN-SOURCE DIODE CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				3	A
Continuous Drain-Source Current		I_{SD}				6	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=3A, V_{GS}=0V			1.4	V
Reverse Recovery Time		t_{rr}	I_F=3A, di/dt = 100A/μs		390		ns
Reverse Recovery Charge		Q_{rr}			2.8		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

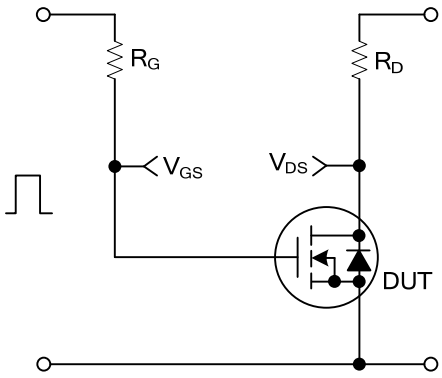


Peak Diode Recovery dv/dt Test Circuit

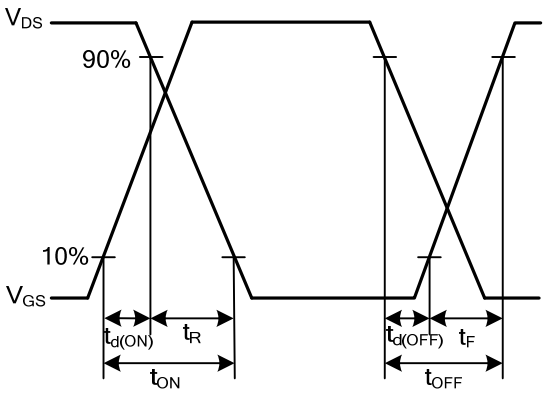


Peak Diode Recovery dv/dt Waveforms

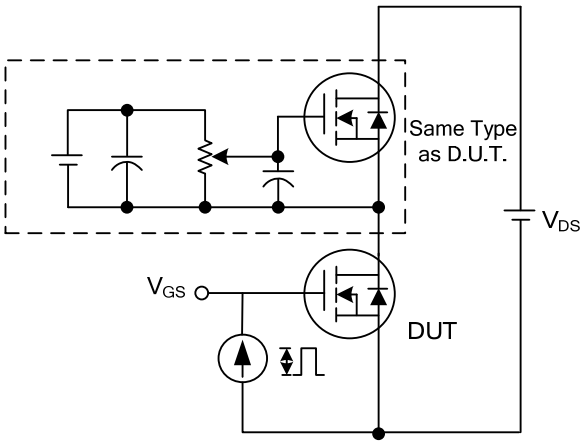
■ TEST CIRCUITS AND WAVEFORMS



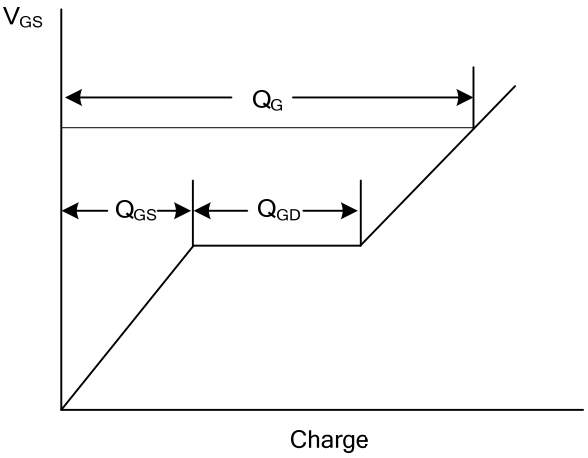
itching Test Circuit



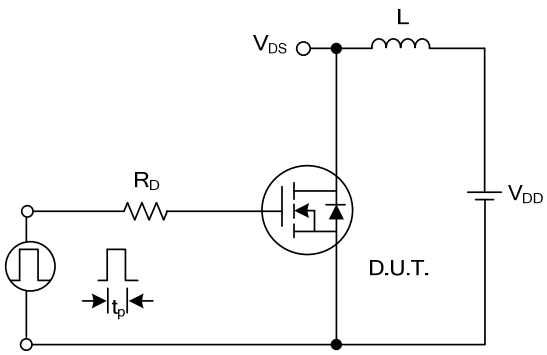
Switching Waveforms



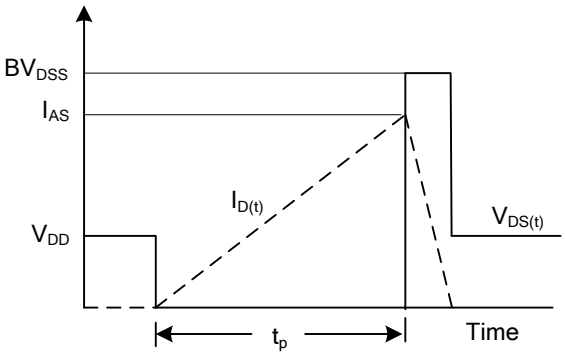
Gate Charge Test Circuit



Gate Charge Waveform



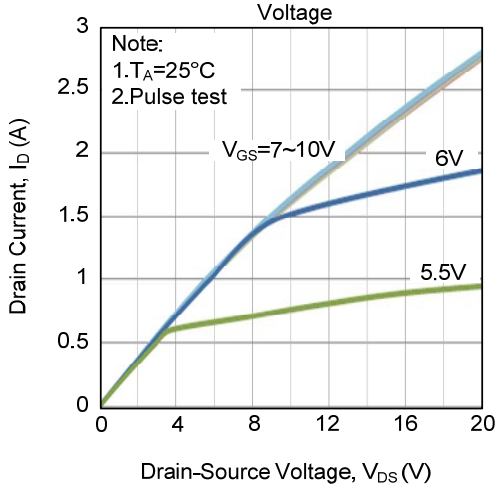
Unclamped Inductive Switching Test Circuit



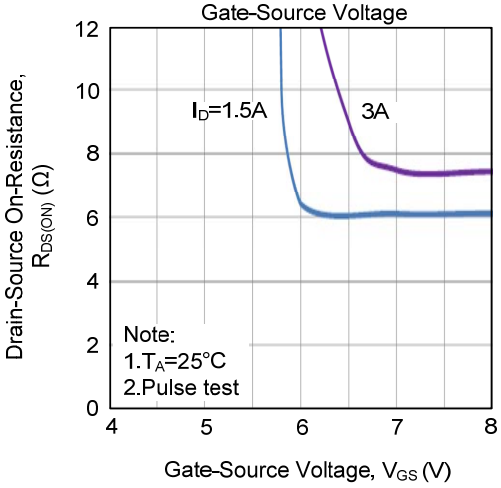
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

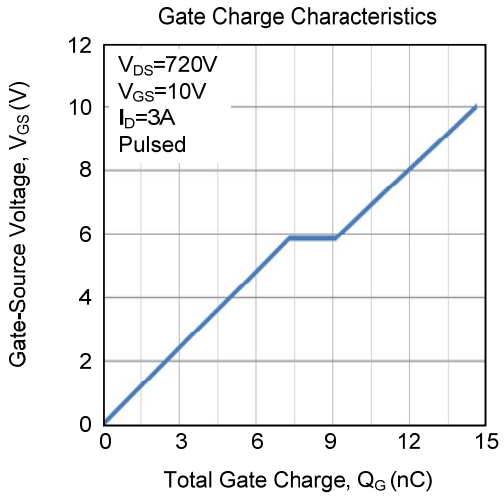
Drain Current vs. Drain-Source Voltage



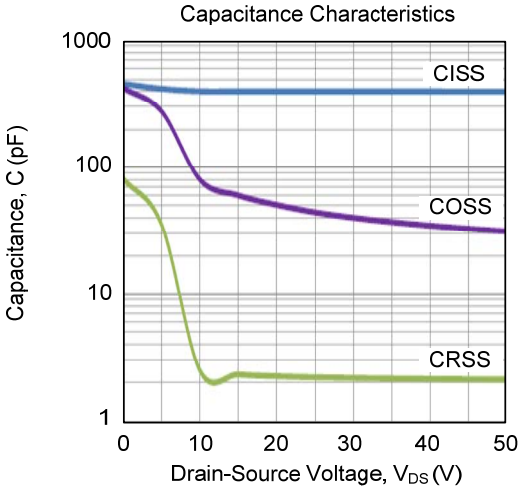
Drain-Source On-Resistance vs. Gate-Source Voltage



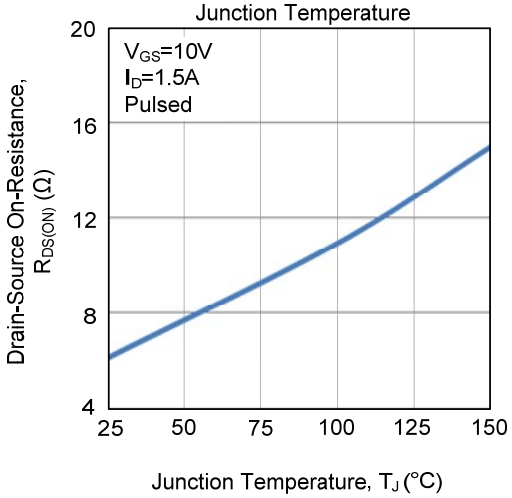
Gate Charge Characteristics



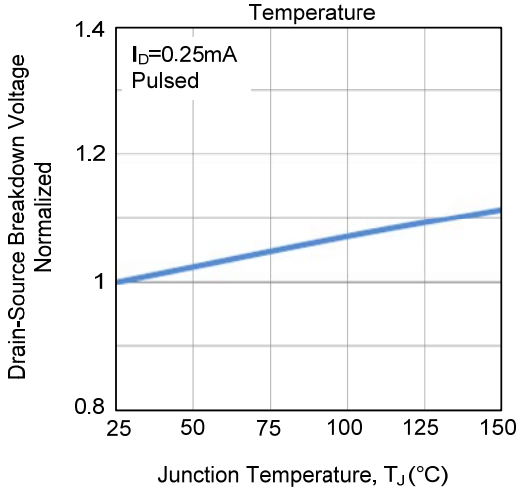
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

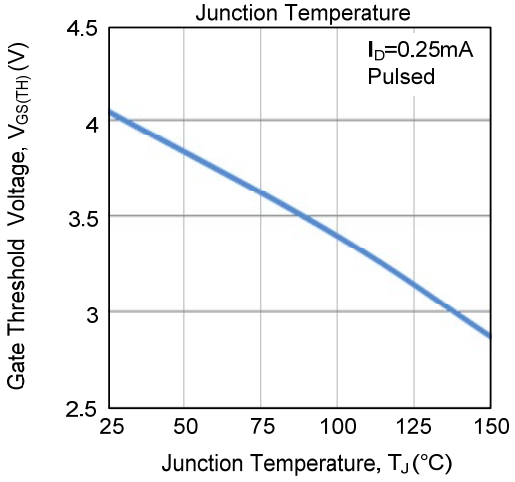


Breakdown Voltage vs. Junction Temperature

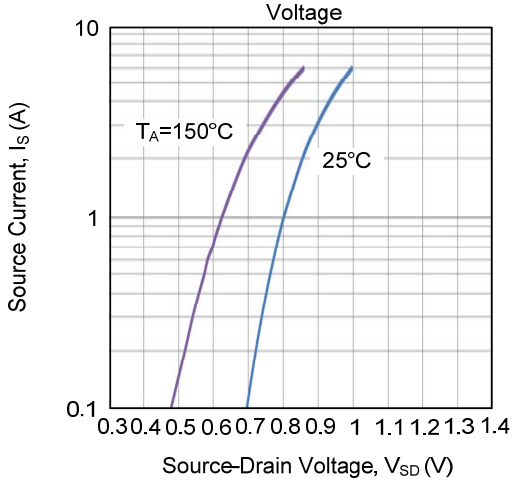


■ TYPICAL CHARACTERISTICS (Cont.)

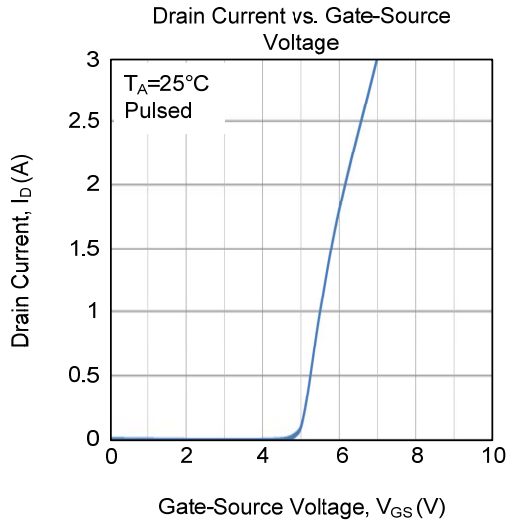
Gate Threshold Voltage vs. Junction Temperature



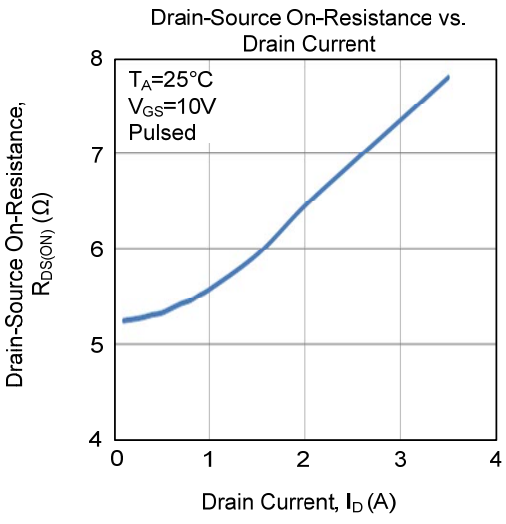
Source Current vs. Source-Drain Voltage



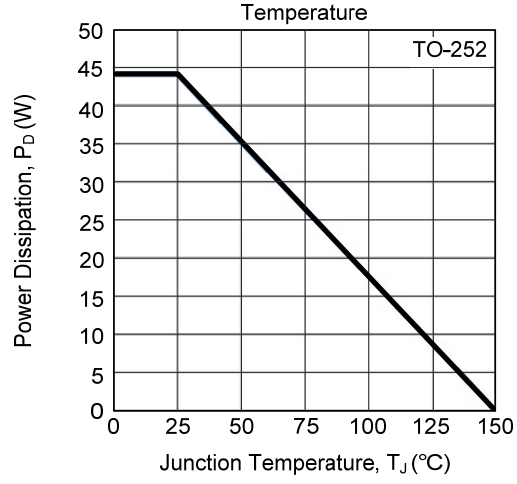
Drain Current vs. Gate-Source Voltage



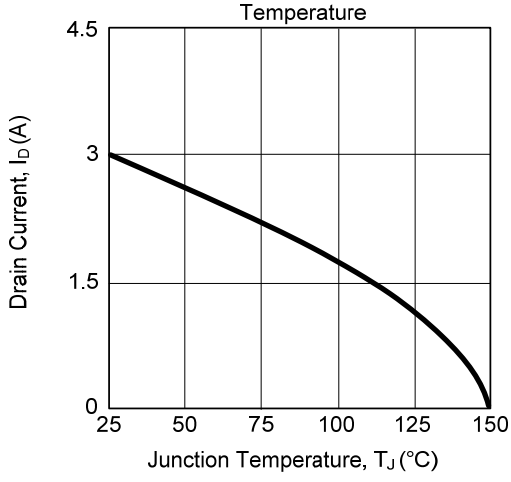
Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Junction Temperature



Drain Current vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)